

KSC3076

I-PACK 1. Base 2. Collector 3. Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_{C}=25^{\circ}C$ unless otherwise noted

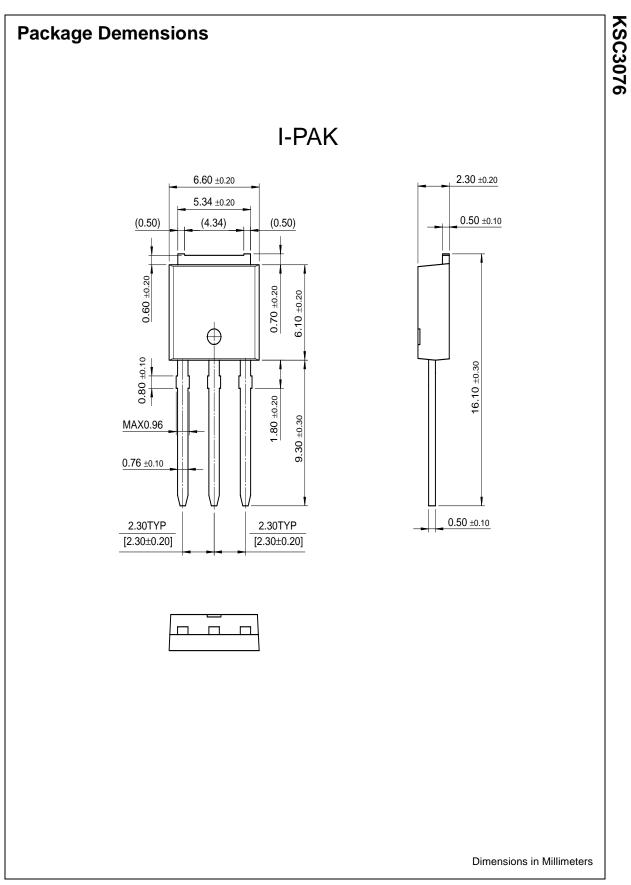
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	2	А
I _B	Base Current	1	А
P _C	Collector Dissipation (T _a =25°C)	1	W
P _C	Collector Dissipation (T _C =25°C)	10	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA, I _B = 0	50			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 50V, I_E = 0$			1	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			1	μΑ
h _{FE1} h _{FE2}	DC Current Gain	$V_{CE} = 2V, I_{C} = 0.5A$ $V_{CE} = 2V, I_{C} = 1.5A$	70 40		240	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 1A, I _B = 0.05A			0.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 1A, I _B = 0.05A			1.2	V
f _T	Current Gain Bandwidth Product	V _{CE} = 2V, I _C = 0.5A		100		MHz
C _{ob}	Output Capacitance	V _{CB} = 10V, f = 1MHz		30		pF
t _{ON}	Turn ON Time	V _{CC} = 30V, I _C = 1A		0.1		μs
t _{STG}	Storage Time	1 _{B1} = - I _{B2} = 0.05A		1		μs
t _F	Fall Time	$R_L = 30\Omega$		0.1		μs

h_{FE1} Classification

Classification	0	Y	
h _{FE1}	70 ~ 140	120 ~ 240	



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